



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	2 x 40 A
V_{RRM}	30 V
T_{j (max)}	150 °C
V_{F (max)}	0.38 V

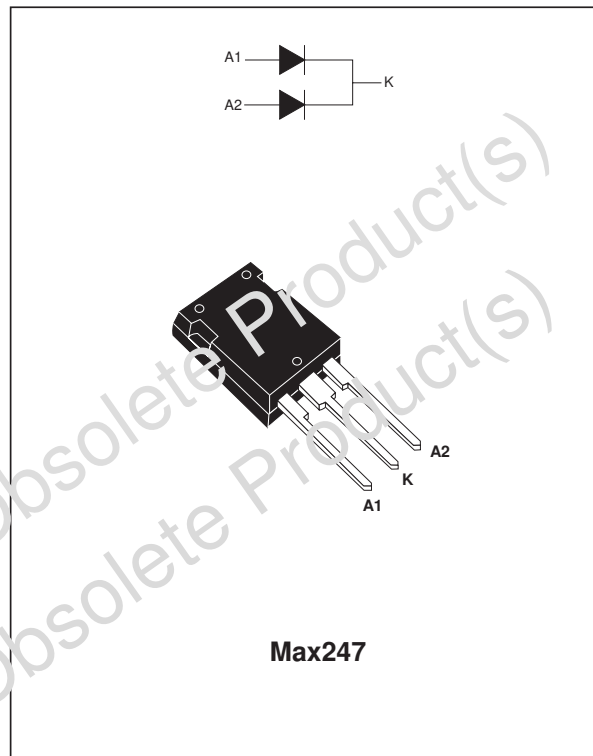
FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- EXTREMELY FAST SWITCHING
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tap Schottky rectifier suited for CAD computers and servers.

Packaged in Max247, this device is intended for use in low voltage, high frequency switching power supplies, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit	
V _{RRM}	Repetitive peak reverse voltage		30	V	
I _{F(RMS)}	RMS forward current		56	A	
I _{F(AV)}	Average forward current	T _c = 130°C	Per diode	40	A
		δ = 0.5	Per device	80	
I _{FCM}	Surge non repetitive forward current	tp = 10 ms sinusoidal	400	A	
I _{RRM}	Repetitive peak reverse current	tp = 2 μs F = 1kHz square	2	A	
P _{ARM}	Repetitive peak avalanche power	tp = 1 μs T _j = 25°C	13000	W	
T _{stg}	Storage temperature range		- 55 to + 150	°C	
T _j	Maximum operating junction temperature		150	°C	
dV/dt	Critical rate of rise of reverse voltage		10000	V/μs	

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

STPS80L30CY

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	0.7	$^{\circ}\text{C}/\text{W}$
		Total	0.5	
$R_{th(c)}$		Coupling	0.3	

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			4	nA
		$T_j = 125^{\circ}\text{C}$		0.7	1.5		
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 40 \text{ A}$			0.43	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 40 \text{ A}$		0.34	0.38	
		$T_j = 25^{\circ}\text{C}$	$I_F = 80 \text{ A}$			0.58	
		$T_j = 125^{\circ}\text{C}$	$I_F = 80 \text{ A}$	0.48	0.53		

Pulse test : * $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :
 $P = 0.23 \times I_{F(AV)} + 0.0037 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

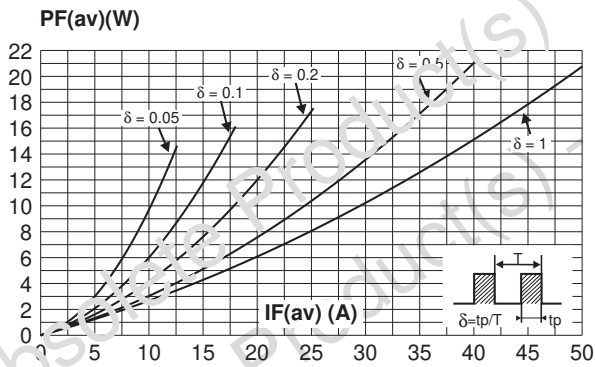


Fig. 3: Normalized avalanche power derating versus pulse duration.

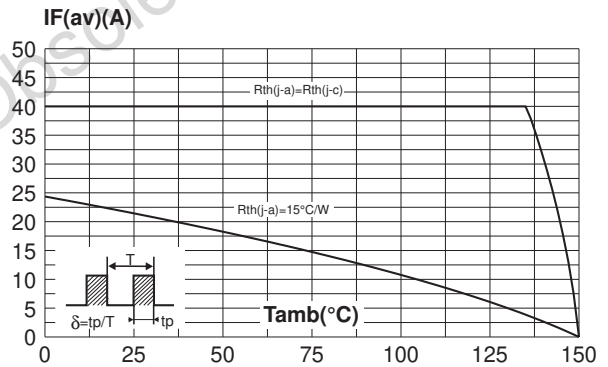


Fig. 4: Normalized avalanche power derating versus junction temperature.

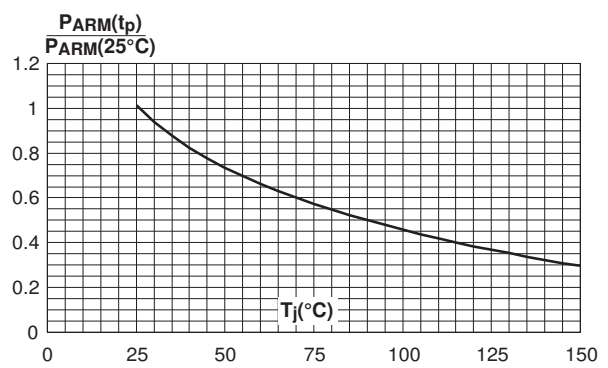
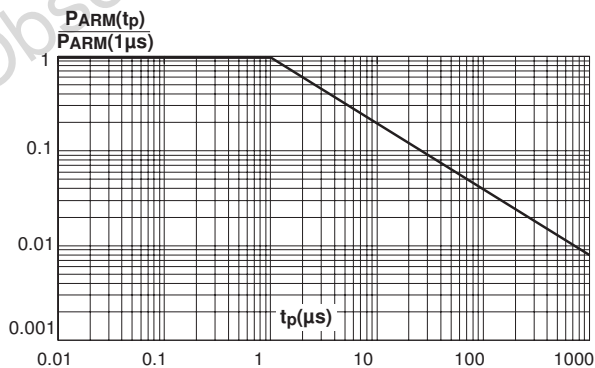


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

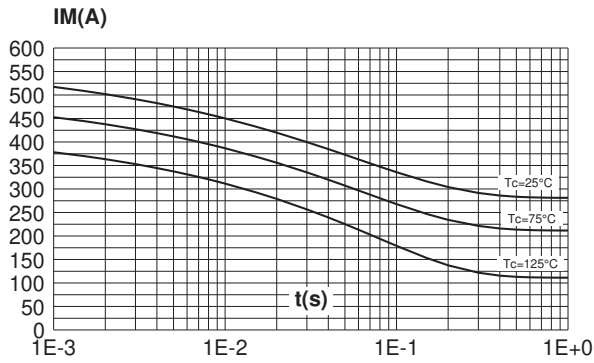


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

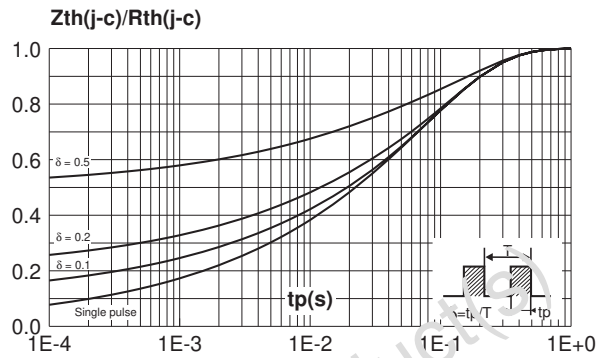


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

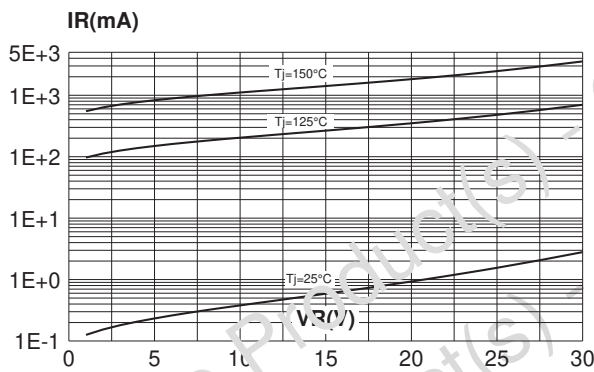


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

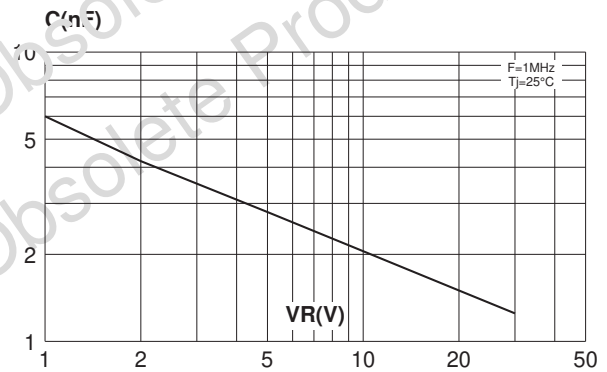
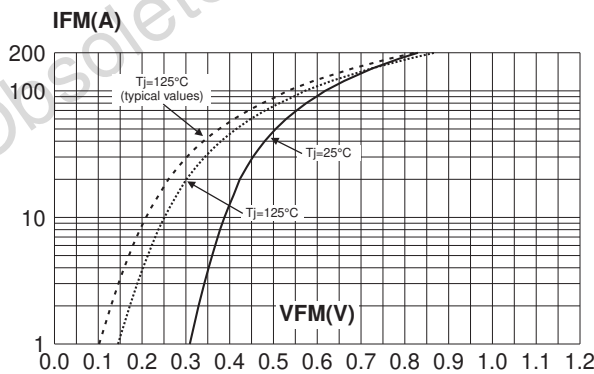


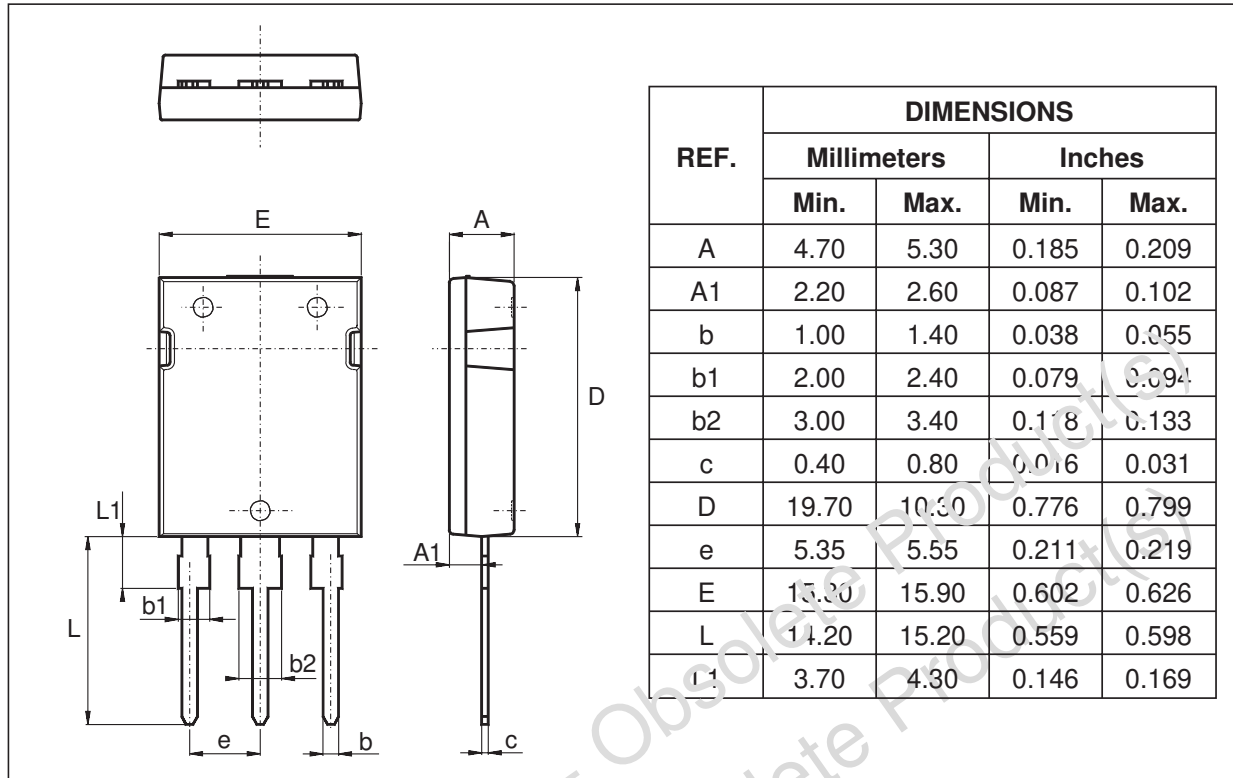
Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).



STPS80L30CY

PACKAGE MECHANICAL DATA

Max247



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS80L30CY	STPS80L30CY	Max247	4.4 g	30	Tube

- EPOXY MEETS UL94 V0
- COOLING METHOD: C

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.

STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany
 Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore
 Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>